

IN THE CLAIMS

Please amend Claim 1 as shown in marked-up form in Appendix A
and in clean-form as follows:

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1. (Amended) A semiconductor device comprising a bond pad structure, which bond pad structure comprises a bond pad disposed above at least one layered structure, wherein the layered structure comprises a metal layer and a layer of a dielectric material, characterized in that via lines are present in the layer of dielectric material, which via lines are arranged in such a way that the metal layers and the via lines form all isolated areas filled with the dielectric material.

REMARKS

This application has been carefully reviewed in light of the Office Action dated April 5, 2002. Claims 1-7 remain pending in this application. Claim 1 is the independent claim. Favorable reconsideration is respectfully requested.

In response to the Office Actions objection to the disclosure, Applicants respectfully believe the attached substitute specification satisfies the objection. As per 37 C.F.R. § 1.125, a marked-up copy and a clean copy are contained herein in Appendices B and C, respectively. Further, the substitute specification contains no new matter. Withdrawal of the objection to the disclosure is respectfully requested.